



Catalogue of Solid-State Radiation Sensors and Summary of User Requirements

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This presentation will be focused mainly on Procurement details.

For more technical details see RADMON webpage



Recent Work ...



- Aug. 2004 - Low-rate irradiation in mixed field and long-term annealing in PS-T7 area;
- Nov. 2004 - Presentation of sensors selected and available for LHC startup;
- Dec. 2004 – work on packaging intensified;
- Jan/Feb. 2005 – Procurement details clarified;
- Mar. 2005 - Sensor Catalogue distributed.

Sensor Catalogue



<http://lhc-expt-radmon.web.cern.ch/lhc-expt-radmon/>

Index of available
sensors

Catalogue Updates
(last 15/3/05)

LHC Experiment Radiation Monitoring (RADMON)

Solid-State Radiation Sensor Working Group

[Sensor Catalogue \(PDF\)](#)

(DATA COMPILATION OF SOLID-STATE SENSORS FOR RADIATION MONITORING)

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CATALOGUE VERSIONS HISTORY

| DATE | VERSION | COMMENTS |
|----------|---------|-------------------------------|
| 01/03/05 | 3.0 | First Draft Version Published |



Sensor Catalogue



<http://lhc-expt-radmon.web.cern.ch/lhc-expt-radmon/>

For each listed sensor:

1. Physical / geometrical data (connectivity);
2. Readout details (schematic examples);
3. Pre- and after- irradiation characteristics;
4. Radiation responses;
5. Handling and operation precautions (temperature, magnetic field)
6. Packaging options and commercial details.

→ Appendices with **Technical Specifications for Procurement.**

RadFET Sensors

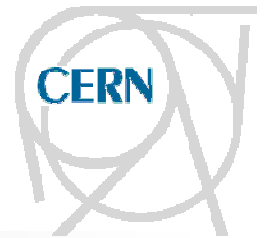


Nine products were evaluated to suit experiments requirements:

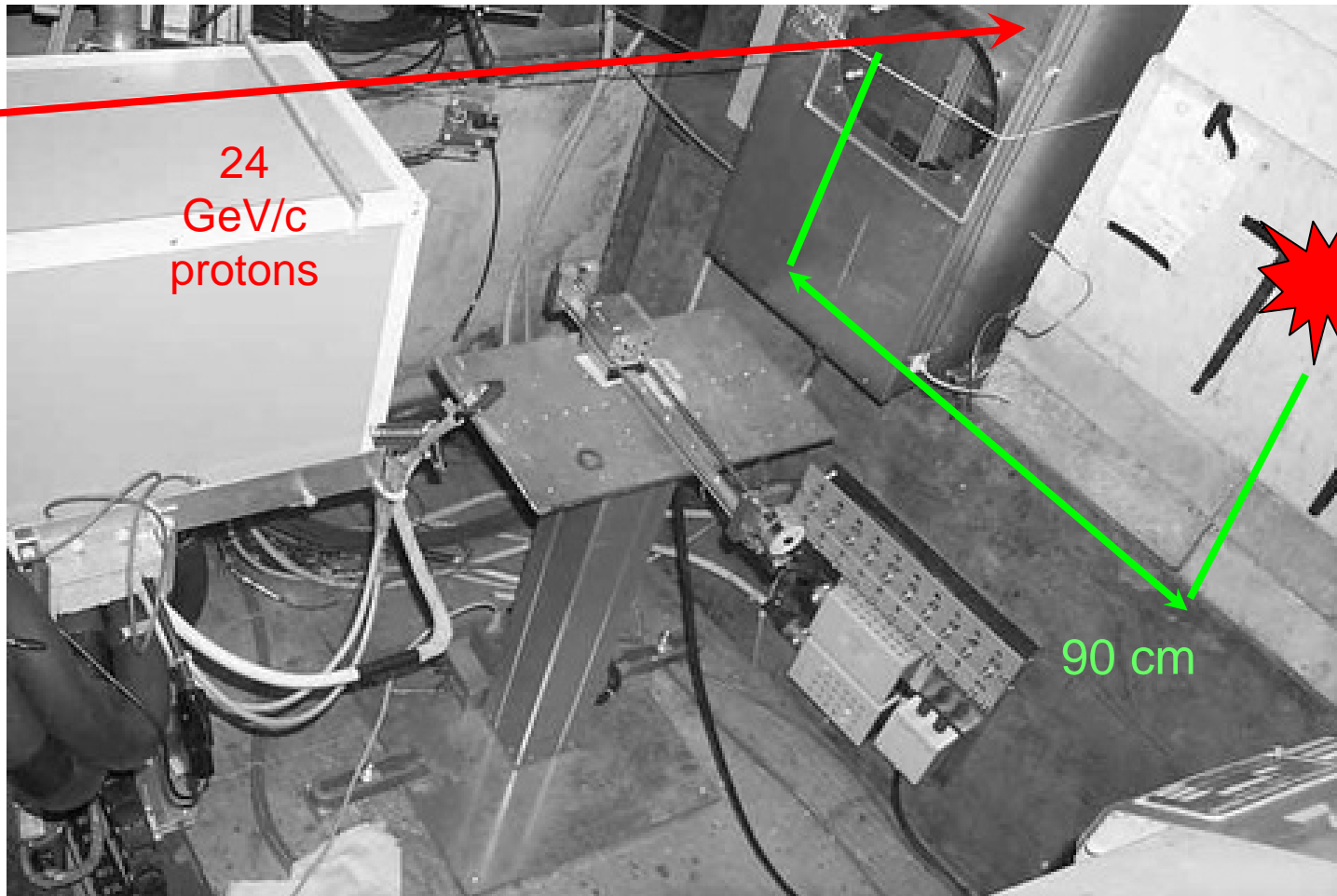
- Thin-Oxide RadFET dies (0.25 μm):
 - “low” sensitivity – high dynamic range;
 - Minimize SiO_2 recombination effects \rightarrow mixed-LET particle fields;
 - Suited for dosimetry in inner-detector regions.

- Thick-Oxide RadFET dies (1.6 μm):
 - “high” sensitivity – low dynamic range;
 - Measurement in “conventional” ($\gamma + n$) radiation fields.
 - Suited for dosimetry in outer-detector regions;

RadFETs: a real application ...



MONITORING OF THE PRIMARY AREA PS-T7 29/9/04 – 18/3/05



24
GeV/c
protons

Monitoring
Location
RadFETs +
ALANINE

γ (>100 keV):
16 ÷ 560 mGy/h

on average:

\underline{n} (<50 keV):
 $3.2 \times 10^{10} \text{ cm}^{-2} \text{ h}^{-1}$

HEP (>100 MeV):
 $3.1 \times 10^7 \text{ cm}^{-2} \text{ h}^{-1}$

RadFETs: Calibration



- At the “90 cm location” alanine should be a good benchmark:

$$d_{n,LE} < 1 \% d_{TOT}$$

$$d_{Alanine} = d_{\gamma,HE} + (\sim 0.1) \times K_{n,LE} \times \Phi_{n,LE} + K_{HEP} \times \Phi_{HEP} \quad (K_{n,LE}^I \ll K_{n,LE})$$

$$d_{RadFET} = d_{\gamma,HE} + (\sim 0.6) \times K_{n,LE}^I \times \Phi_{n,LE} + K_{HEP}^I \times \Phi_{HEP} \quad (K_{HEP}^I \sim K_{HEP})$$

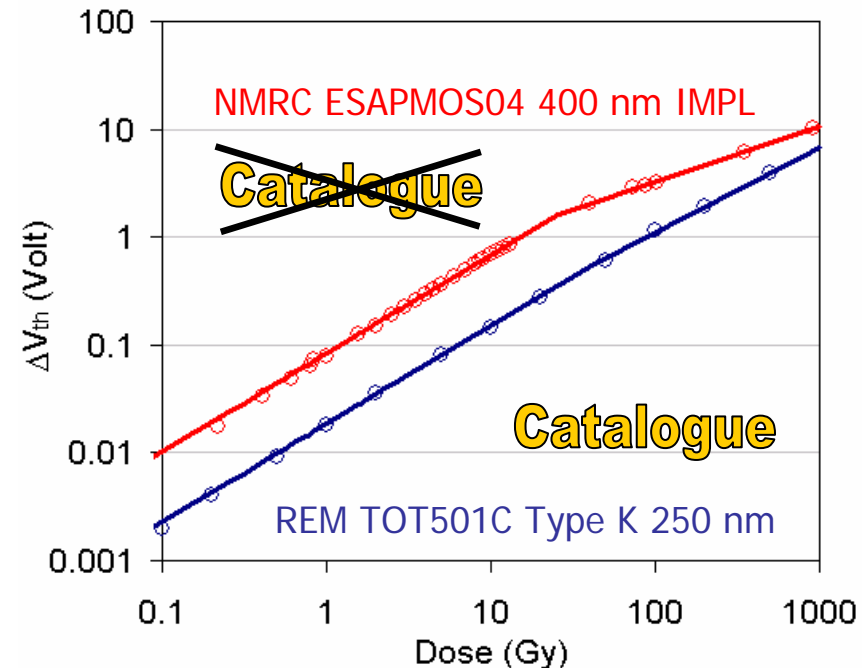
- RadFETs Signal-to-Dose Conversion:

γ -Calibration based on CERN, ESTEC and suppliers to obtain the parameters a_n, b_n

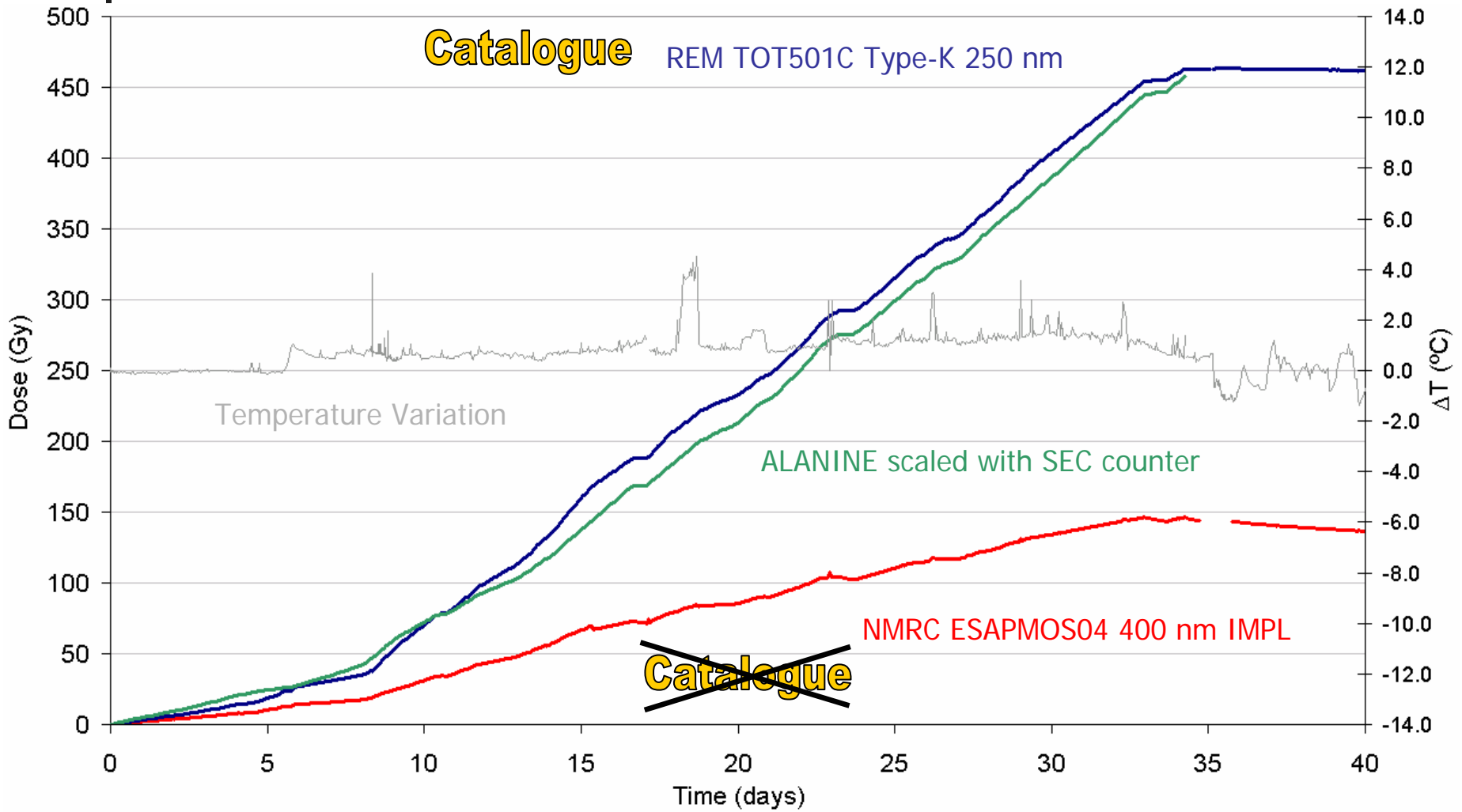
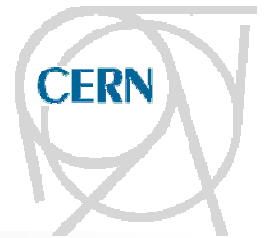
$$\text{Dose} = C_1 \times \{[\Delta V_{th}(T) / a_1]^{1/b_1}\} + C_2 \times \{[\Delta V_{th}(T) / a_2]^{1/b_2}\}.$$

$$C_1 = 1 \text{ and } C_2 = 0 \text{ for } \Delta V_{th} \leq V_0$$

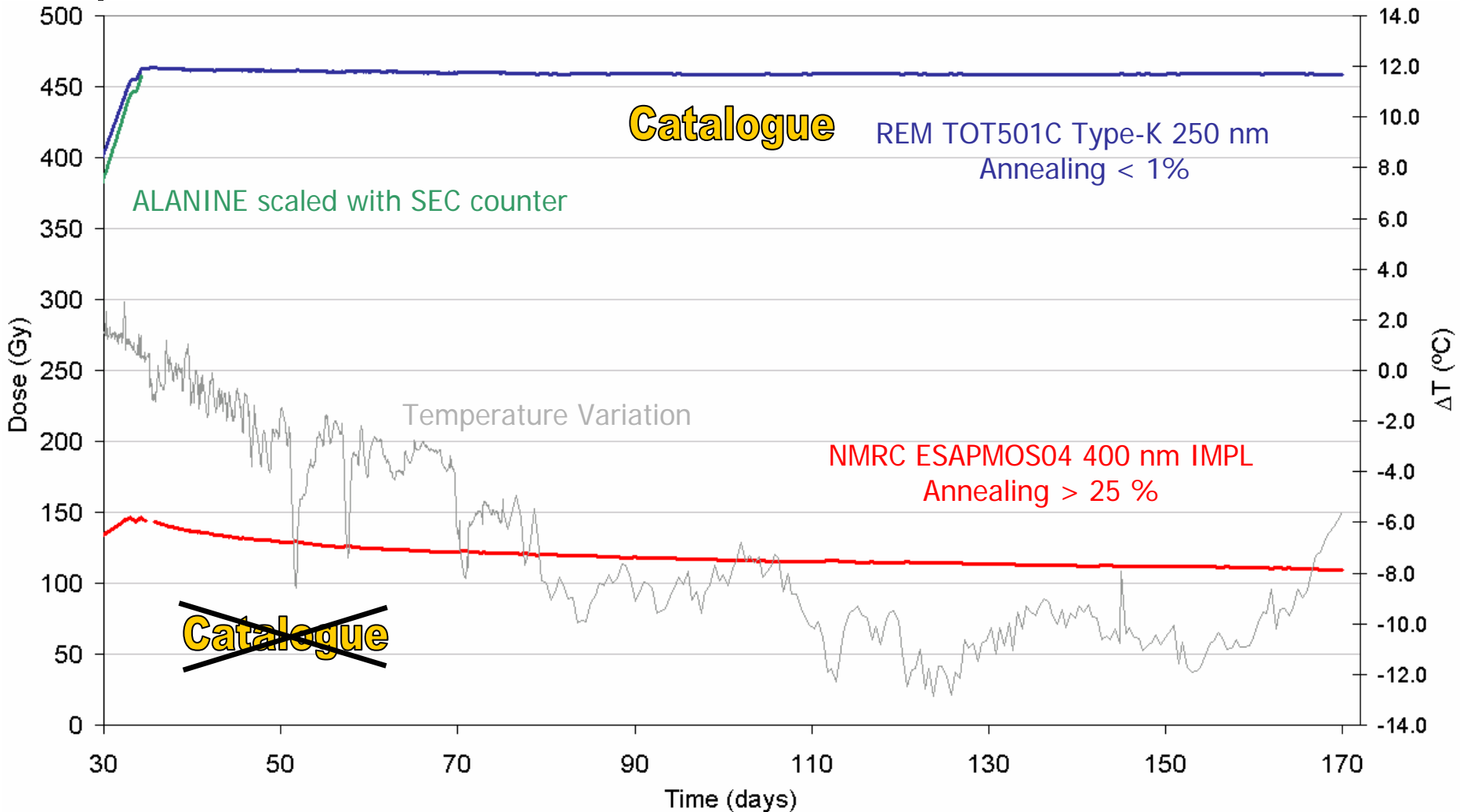
$$C_1 = 0 \text{ and } C_2 = 1 \text{ for } \Delta V_{th} > V_0$$



RadFETs: Irradiation



RadFETs: Shutdown





RadFETs: Comments



Origin of the presented mismatch for some types of RadFETs:

- a. Some oxides show saturation phenomena in hadron fields;
- b. Strong RT annealing plays a substantial role over long times;

Additional data-treatment could be a “work-around” to scale the data,
however

- a. The understanding and the evaluation of scaling factors is still an open issue (Nowadays data match only up to low doses/short times!)
- b. Fading correction must be implemented (very complex! unreliable?).

Easy and Reliable measurements over long-times can be performed up to high doses in LHC experiments if devices are carefully selected!



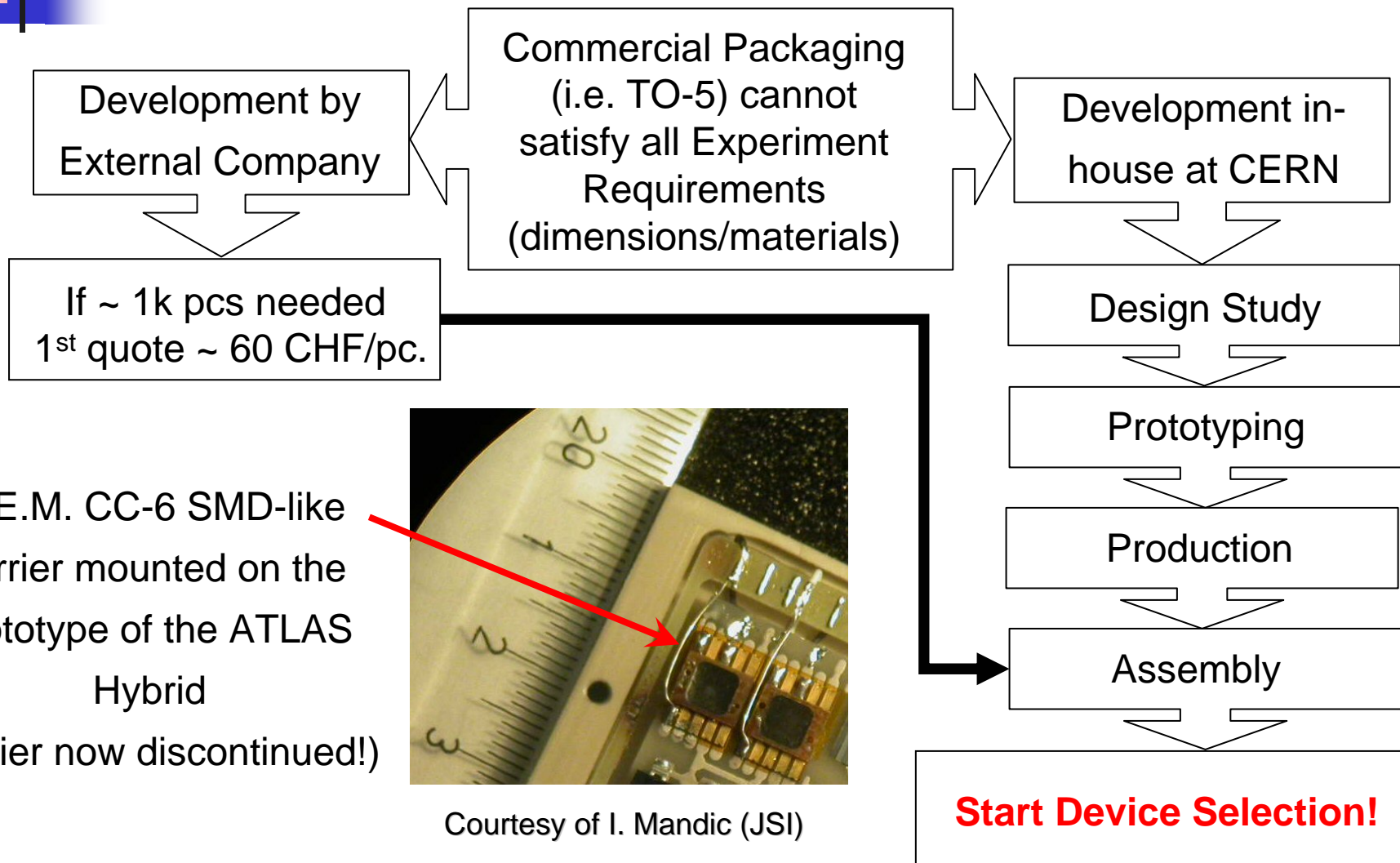
RadFETs: Quotes



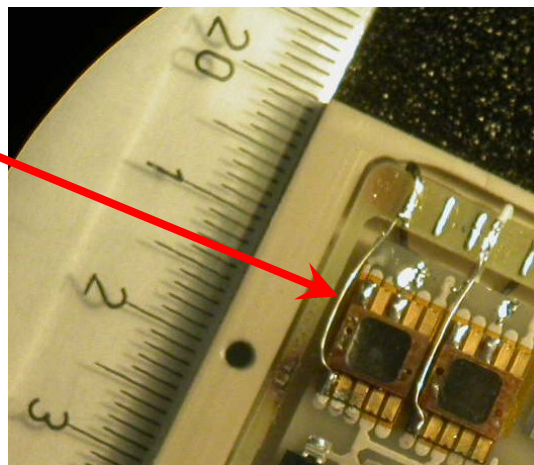
- Thin-Oxide RadFET dies (0.25 μm):
 - Purchase of remaining 600 samples of the REM TOT501C wafer;
 - Unselected stock of diced devices → **Appropriate packaging needed!**
 - CERN accurate selection procedure and QA needed;
 - ~ 60 CHF/pc. (working device: quantity/yield dependence).

- Thick-Oxide RadFET dies (1.6 μm):
 - Purchase of 100 samples of the LAAS 1600 MOSFET wafer;
 - Selected stock of diced (TO-5) devices → **Appropriate packaging needed!**
 - 60 CHF/pc.
 - Prompt delivery for 100 pcs reserved;

RadFETs: Packaging



R.E.M. CC-6 SMD-like carrier mounted on the prototype of the ATLAS Hybrid (carrier now discontinued!)



Courtesy of I. Mandic (JSI)

p-i-n Si-diodes



➤ High-Sensitivity [$\Phi_{eq} < 2 \times 10^{12} \text{ cm}^{-2}$] Si-diode (**Forward**):

- Low-rate data analysis ongoing: no problem at the moment!
- Purchase of 100 samples in prompt delivery;
- Selected stock of packaged devices (\varnothing 3 mm \times 3 mm);
- 100 USD/pc (117 CHF/pc).

➤ BPW 34F Si-diode [$\Phi_{eq} > 2 \times 10^{12} \text{ cm}^{-2}$] (**Forward**):

- Readout protocol under definition;
- pre-irradiation seems the solution to go for lower fluences!
- More annealing studies are ongoing;
- A coordinate purchase may avoid in homogeneity problems.
- ~ 2 CHF/pc.

$p-i-n$ Si-diodes



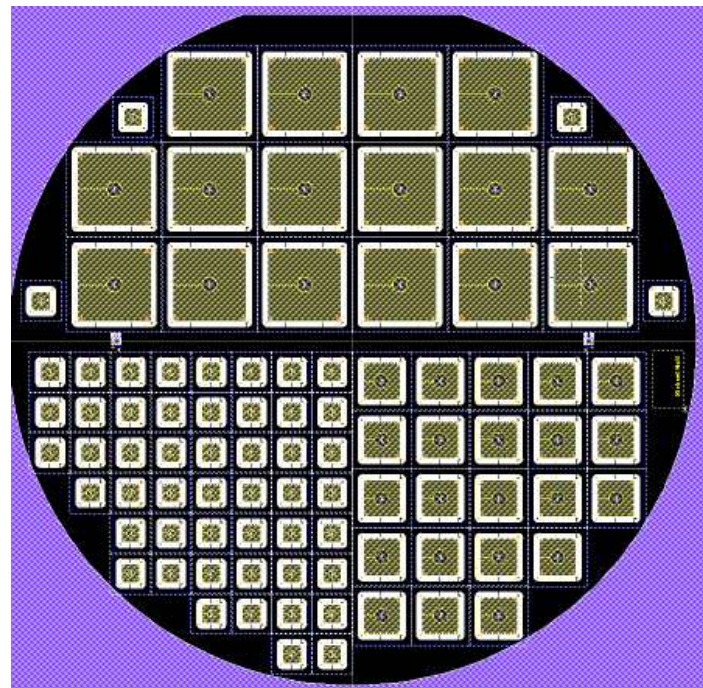
➤ Particle Detector diode (Reverse):

- ~ 200 bare samples from ST Microelectronics on stock.
- Unselected stock of diced devices: selection procedure and QA needed;
- 30 CHF/pc.

➤ New Particle Detector structure (Reverse):

A sensor mask has already been designed.

3 detector sizes: from 2.5 to 10 mm²



Experiments

Sensor-Requirements



| | Status | Thin Oxide FETs | Thick Oxide FETs | High Sensitivity p-i-n | BPW 34 p-i-n | Si-Detector p-i-n |
|-------|---------------|---|------------------|------------------------|--------------|-------------------|
| ALICE | March 2005 | 10 | 20 | 30 | 0 | 0 |
| ATLAS | February 2005 | 36 [ID] (18+18) | 100 [RoA] | 36 [ID] 100 [RoA] | 20 [ID] | 0 |
| CMS | March 2005 | a few ? | a few ? | a few ? | / | / |
| LHCb | March 2005 | 30 | 30 | 50 | 30 | 0 |
| TOTEM | March 2005 | A contact-person is going to be appointed | | | | |

[ID] = Inner Detector; [RoA] = Rest of Atlas

Conclusion & Future Steps



- First version of “Sensor Catalogue” has been presented containing devices available for LHC startup:
 - 2 x RadFETs dosimeters;
 - 2 x p-i-n diodes (Forward operation);
 - 1 x p-i-n diodes (Reverse operation).

- In contact with all suppliers: preliminary offers received, prices will depend on quantities;

- Working on packaging options started: needs input from experiments!

- **We are going to order devices by middle of April 2005.**